

## Si1032X-T1-GE3-VB Datasheet

### N-Channel 20 V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>c</sup>	$Q_g$ (TYP.)
20	0.270 at $V_{GS} = 4.5$ V	0.85	1.4 nC
	0.390 at $V_{GS} = 2.5$ V	0.70	

#### FEATURES

- Trench power MOSFET
- 100 %  $R_g$  tested

#### APPLICATIONS

- Smart phones, tablet PC's
  - DC/DC converters
  - Boost converters
  - Load switch, OVP switch



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	$\pm 12$	
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ )	$T_C = 25^\circ\text{C}$	$I_D$	0.85	A
	$T_C = 70^\circ\text{C}$		0.65	
	$T_A = 25^\circ\text{C}$		0.7 <sup>a, b</sup>	
	$T_A = 70^\circ\text{C}$		0.6 <sup>a, b</sup>	
Pulsed Drain Current ( $t = 300 \mu\text{s}$ )		$I_{DM}$	6	
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	$I_S$	0.4	
	$T_A = 25^\circ\text{C}$		0.3	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	0.5	W
	$T_C = 70^\circ\text{C}$		0.3	
	$T_A = 25^\circ\text{C}$		0.4 <sup>a, b</sup>	
	$T_A = 70^\circ\text{C}$		0.3 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)			260	

#### THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient <sup>a, d</sup>	$t \leq 10$ s	$R_{thJA}$	250	300	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	225	270	

#### Notes

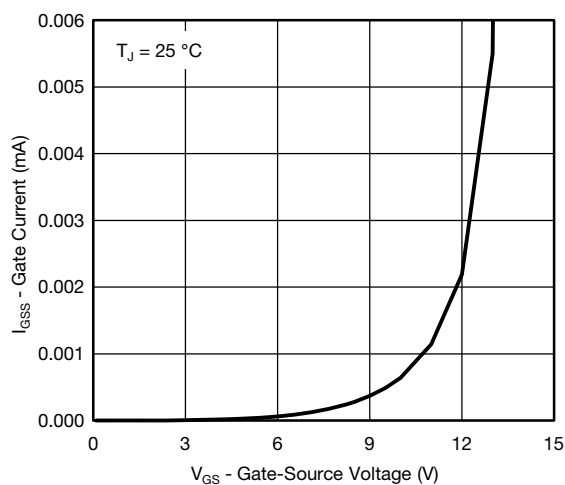
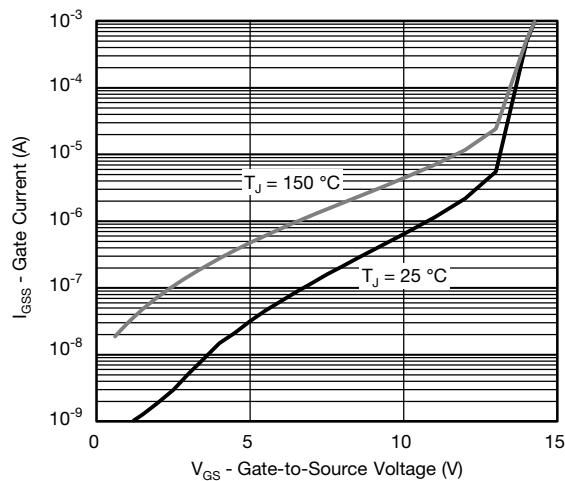
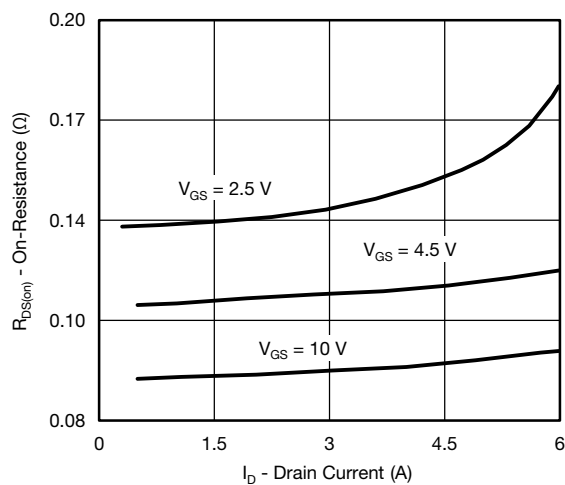
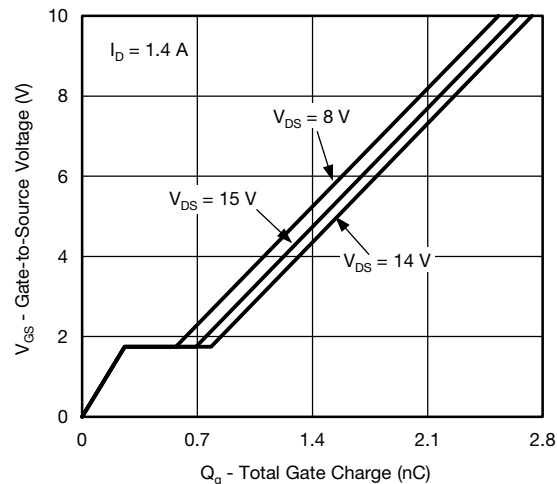
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- Based on  $T_C = 25^\circ\text{C}$ .
- Maximum under steady state conditions is  $360^\circ\text{C/W}$ .

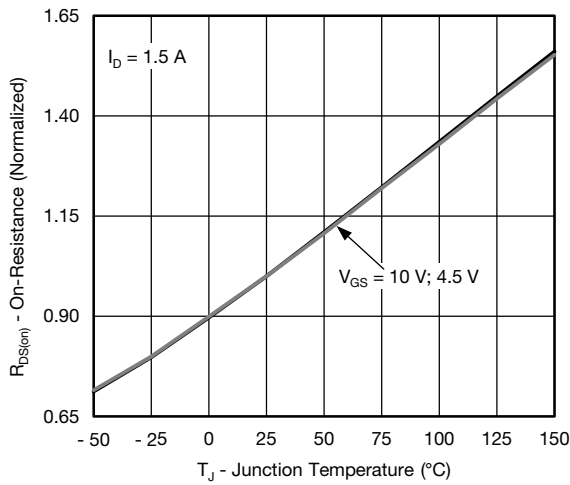
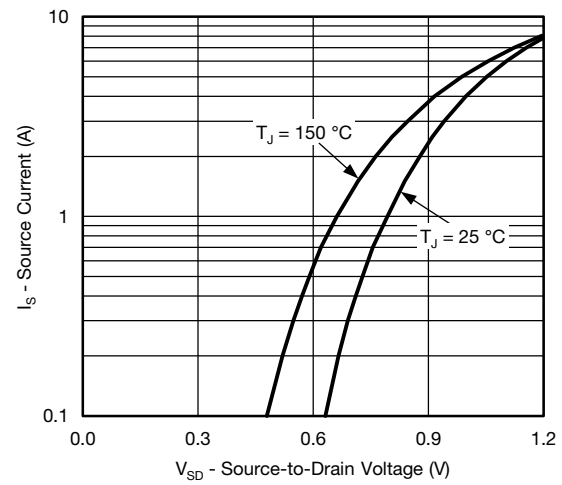
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	32	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-3	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.5	-	1.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 4.5 V	-	-	0.1	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V	-	-	± 20	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	-	0.1	
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	2	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1 A	-	0.270	-	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.5 A	-	0.390	-	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.4 A	-	5	-	S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	105	-	pF
Output Capacitance	C <sub>oss</sub>		-	23	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	11	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.4 A	-	2.7	4.1	nC
		V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1.4 A	-	1.4	2.1	
Gate-Source Charge	Q <sub>gs</sub>		-	0.3	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.5	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.4	7	14	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 13.6 Ω I <sub>D</sub> ≅ 1.1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	2	4	ns
Rise Time	t <sub>r</sub>		-	9	18	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	8	16	
Fall Time	t <sub>f</sub>		-	8	16	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 13.6 Ω I <sub>D</sub> ≅ 1.1 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	8	16	
Rise Time	t <sub>r</sub>		-	13	20	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	23	
Fall Time	t <sub>f</sub>		-	6	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	0.4	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	6	
Body Diode Voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.1 A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.1 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	8	16	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	3	6	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	5	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	3	-	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

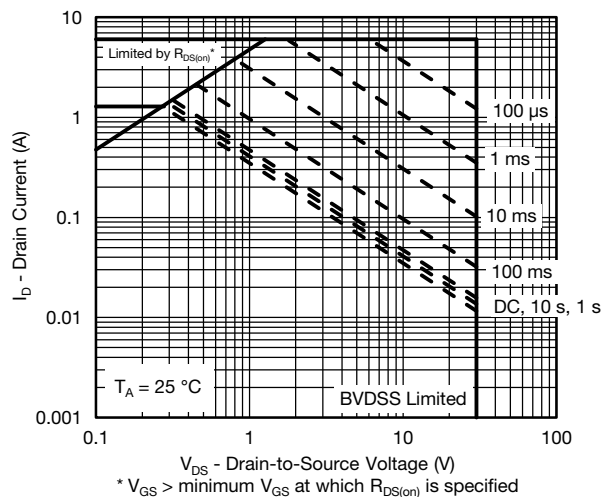
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

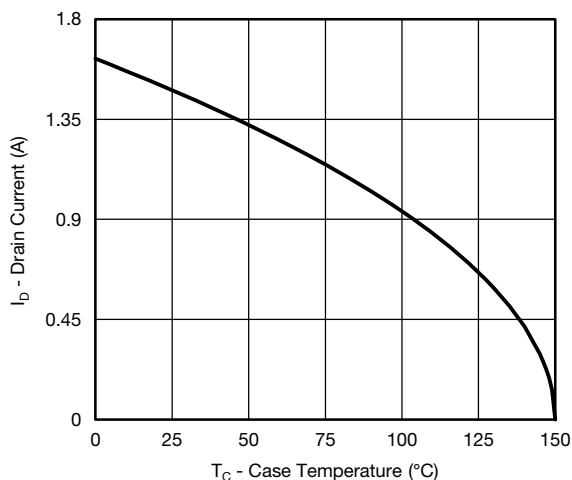
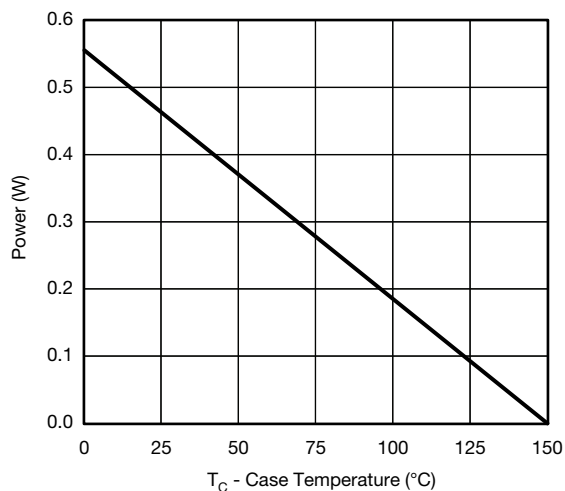
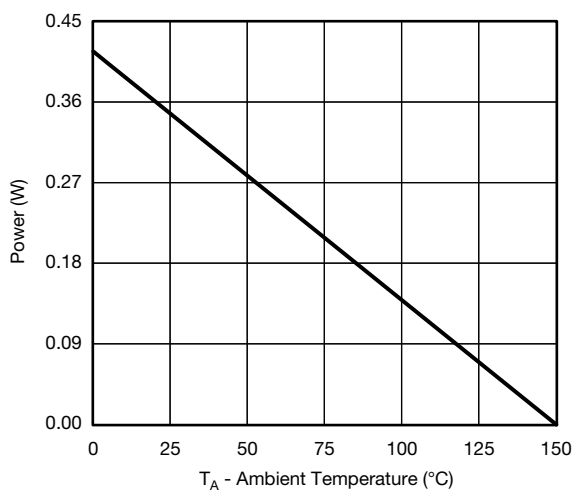
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Gate Source Voltage vs. Gate Current****Gate Source Voltage vs. Gate Current****Output Characteristics****On-Resistance vs. Drain Current****Transfer Characteristics****Gate Charge**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

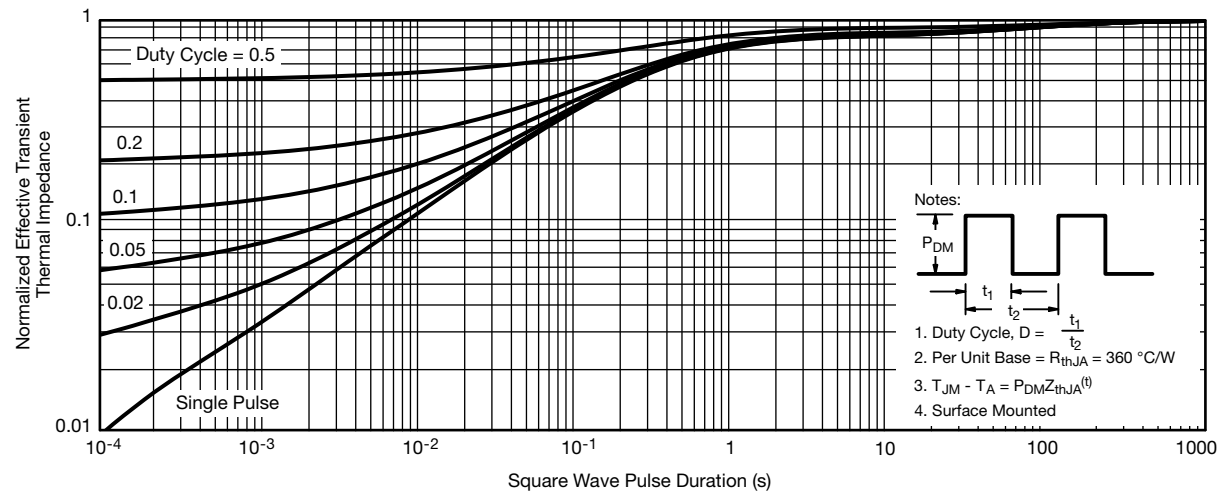
**Threshold Voltage**

**Single Pulse Power, Junction-to-Ambient**

**Safe Operating Area, Junction-to-Ambient**

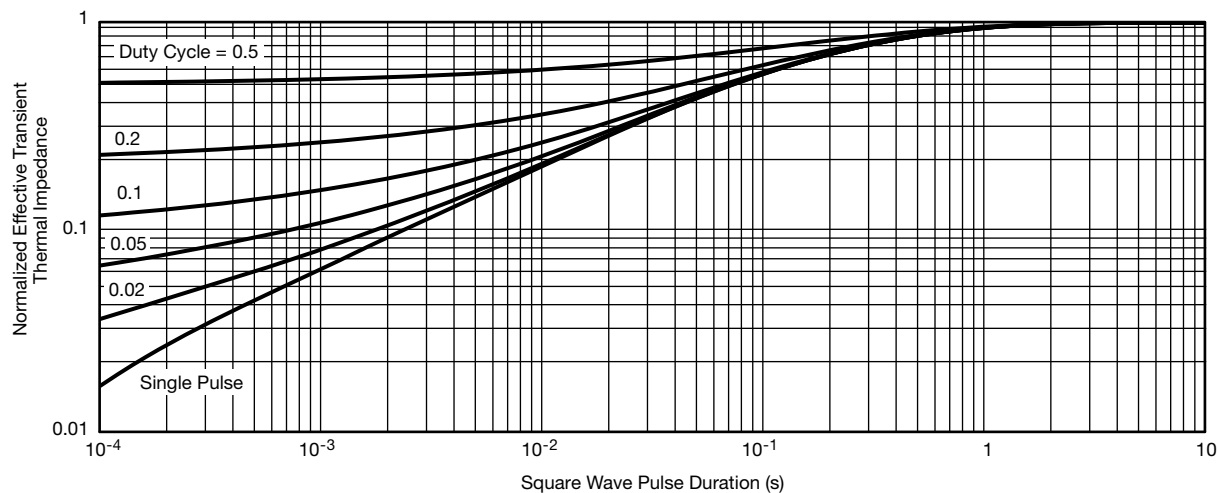
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Current Derating\*****Power, Junction-to-Case****Power, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

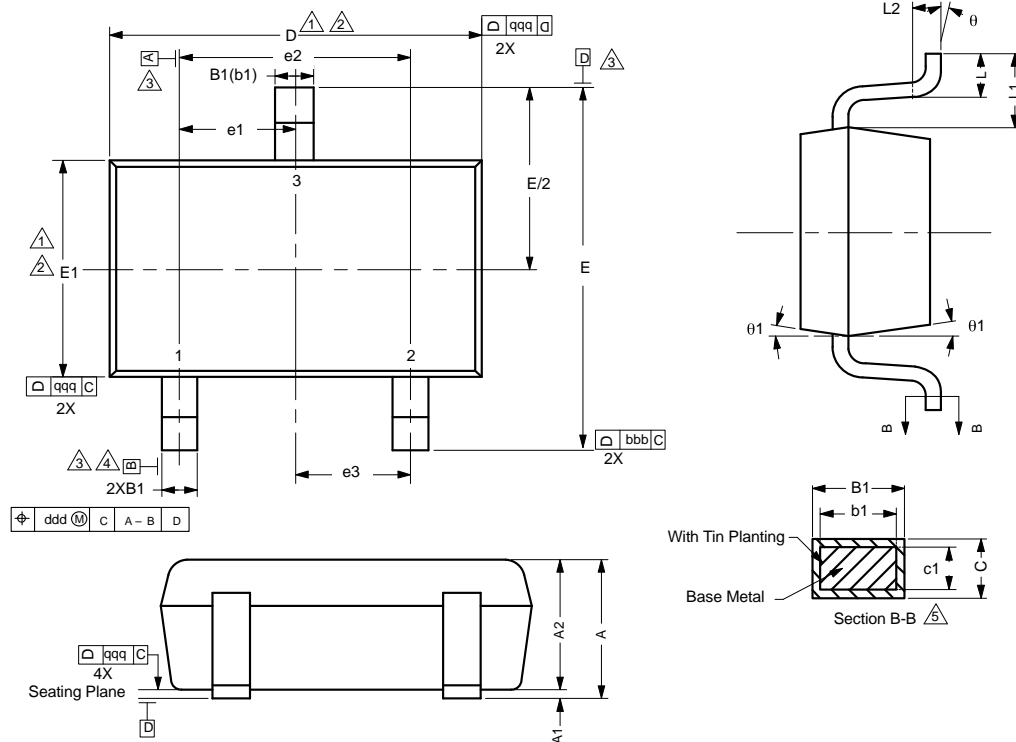


**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

## SC-75A: 3 Leads



### Notes

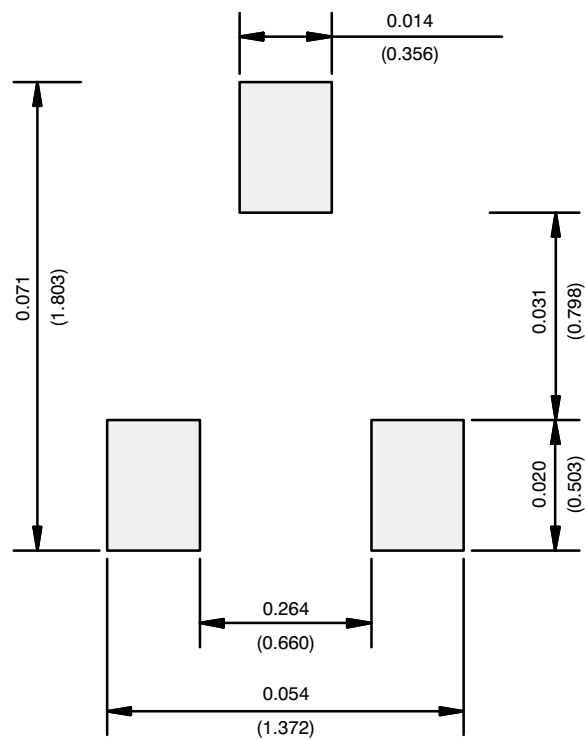
Dimensions in millimeters will govern.

1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. Datums A, B and D to be determined 0.10 mm from the lead tip.
4. Terminal positions are shown for reference only.
5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A <sub>1</sub>	0.00	-	0.10	
A <sub>2</sub>	0.65	0.70	0.80	
B <sub>1</sub>	0.19	-	0.24	5
b <sub>1</sub>	0.17	-	0.21	
c	0.13	-	0.15	5
c <sub>1</sub>	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E <sub>1</sub>	0.66	0.76	0.86	1, 2
e <sub>1</sub>	0.50 BSC			
e <sub>2</sub>	1.00 BSC			
e <sub>3</sub>	0.50 BSC			
L	0.15	0.205	0.30	
L <sub>1</sub>	0.40 ref.			
L <sub>2</sub>	0.15 BSC			
θ	0°	-	8°	
θ <sub>1</sub>	4°	-	10°	

RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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